


NEIFELD IP LAW REFERENCE FORM LIST OF REFERENCES CITED BY THE APPLICANT (Rev: 5/14/2003)	NEIFELD REF: OSEM-DB3	APPLICATION NO: 09/636,484
	FIRST NAMED INVENTOR: BRADDOCK	
	FILING DATE: 8/10/2000	GROUP ART UNIT: 2811

LISTING OF UNITED STATES PATENTS

EXAMINER INITIALS	REFERENCE NUMBER (U SERIES)	PATENT NUMBER	ISSUE DATE	NAME OF PATENTEE OR APPLICANT	PAGE/LINE AND FIGURE/ELEMENT OF RELEVANT MATERIAL AND/OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
DNIC	U-1	3,956,373	4-1976	Jones	Already of Record
	U-2	4,404,865	9-1983	Mannervit	Already of Record
	U-3	4,410,983	10-1983	Melik	Already of Record
	U-4	4,416,953	11-1983	Nishizawa et al.	Already of Record
	U-5	4,561,915	12-1985	Mina	Already of Record
	U-6	4,624,901	11-1986	Glass	Already of Record
	U-7	4,671,777	6-1987	van Eaden et al.	Already of Record
	U-8	4,685,193	8-1987	Faria et al.	Already of Record
	U-9	4,746,882	5-1988	Kwok	Already of Record
	U-10	4,802,180	1-1989	Brandt, Jr. et al.	Already of Record
	U-11	4,843,450	6-1989	Kirchner et al.	Already of Record
	U-12	4,859,253	8-1989	Buckman et al.	Already of Record
	U-13	4,935,789	6-1990	Eximilio	Already of Record
	U-14	4,970,060	11-1990	Belt et al.	Already of Record
	U-15	5,055,145	10-1991	Belt et al.	Already of Record
	U-16	5,134,762	6-1992	Childs et al.	Already of Record
	U-17	5,170,407	12-1992	Schubert et al.	Already of Record
	U-18	5,270,798	12-1993	Pao et al.	Already of Record
	U-19	5,323,853	6-1994	Luryi et al.	Already of Record
	U-20	5,386,137	1-1995	Dell et al.	Already of Record
	U-21	5,425,843	6-1995	Holonyuk et al.	Already of Record
	U-22	5,451,548	9-1995	Hunt et al.	Already of Record
	U-23	5,491,712	2-1996	Lin et al.	Already of Record
	U-24	5,550,889	8-1996	Potts et al.	Already of Record
Date:	06-15-05		Examiner's Signature: 		

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<i>DNIC</i>	U-25	5,597,768	1-1997	Paslack et al.	Already of Record
	U-26	5,640,951	6-1997	Faria	Already of Record
	U-27	5,665,658	9-1997	Paslack	Already of Record
	U-28	5,693,565	12-1997	Camilleri et al.	Already of Record
	U-29	5,729,563	3-1998	Wang et al.	Already of Record
	U-30	5,767,388	6-1998	Fleisher et al.	Already of Record
	U-31	5,885,624	9-1998	Yang et al.	Already of Record
	U-32	5,881,171	10-1998	Hong et al.	Already of Record
	U-33	5,838,788	11-1998	Lin et al.	Already of Record
	U-34	5,896,409	4-1999	Corzine et al.	Already of Record
	U-35	5,930,611	7-1999	Okamoto	Already of Record
	U-36	5,945,718	8-1999	Paslack et al.	Already of Record
	U-37	5,953,362	9-1999	Panajiotou et al.	Already of Record
	U-38	6,006,562	12-1999	Bhandari et al.	Already of Record
	U-39	6,028,693	2-2000	Fork et al.	Already of Record
	U-40	6,038,453	2-2000	Paslack et al.	Already of Record
	U-41	6,045,611	4-2000	Isii et al.	Already of Record
	U-42	6,067,908	5-2000	Yuen et al.	Already of Record
	U-43	6,071,580	6-2000	Okamoto et al.	Already of Record
	U-44	6,094,295	7-2000	Paslack et al.	Already of Record
	U-45	6,114,079	9-2000	Christian et al.	Already of Record
	U-46	6,150,677	11-2000	Tanaka et al.	Already of Record
	U-47	6,207,976	3-2001	Takahashi et al.	Already of Record
	U-48	6,252,896	6-2001	Ferr et al.	Already of Record
Date: <i>06-15-05</i>	Examiner's Signature: <i>Langdon</i>				

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LISTING OF NON PATENT LITERATURE

EXAMINER INITIALS	REFERENCE NUMBER (L Series)	PUBLICATION DATE	INCLUDE IN SEQUENCE: Name of first author (in CAPITAL LETTERS), Title in quotation marks, name of publication, date of publication, page numbers, publisher, city of publication, and country of publication	ENGLISH LANGUAGE TRANSLATION ATTACHED? (YES OR NO) AND/OR OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
DNIC	E-1	1994	1995-1996 Alfa-AESAR Catalog, 1994, page 1344, Johnson Matthey Catalog Company, Inc., Ward Hill, MA, US.	Already of Record
	E-2	6-2001	VARGATMAN et al., "Band Parameters for III-V Semiconductors and Their Alloys," J. Appl. Phys. PP 5816-5875 (June 1, 2001).	Already of Record
	E-3	2003	"Gallium Oxide on Gallium Arsenide Atomic Structure, Materials, and Devices," Chapter 12, either published or scheduled for publication in "Gallium Oxide on Gallium Arsenide: Atomic Structure, Materials, and Devices," in III-IV Semiconductor Heterostructures: Physics and Devices, edited by N. Z. Gal, Transworld Research Publisher, Kerala, India (2003).	Already of Record
	E-4	7-1996	PASSLACK et al., "Thermodynamic and photochemical stability of low interface state density Ga ₂ O ₃ -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Vol 69, No 3, pp 302-304, 15 July 1996.	Already of Record
	E-5	6-1997	PASSLACK et al., "Recombination velocity at oxide-GaAs interfaces fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 66, Number 22, pages 3605-3607, 17 June 1997.	Already of Record
	E-6	2-1996	PASSLACK et al., "Quasistatic and high frequency capacitance-voltage characterization of Ga ₂ O ₃ -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 8, pages 1099-1101, 19 February 1996.	Already of Record
	E-7	8-1997	UEDA et al., "Anisotropy of electrical and optical properties in Li-Ga ₂ O ₃ single crystals", Applied Physics Letters, Volume 71, Number 7, Pages 933-935, 18 August 1997.	Already of Record

Date: 06-15-05	Examiner's Signature: <i>Kerry Ray</i>
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DNIC	1-9	6-1997	GEDA et al., "Synthesis and control of conductivity of ultraviolet transmitting B-Ga ₂ O ₃ single crystals", Applied Physics Letters, Volume 70, Number 26, pages 3561-3563, 30 June 1997.	Already of Record
	1-9	2-2000	KHAN et al., "AlGaInGa ₂ N Metal Oxide Semiconductor Heterostructure Field Effect Transistor", IEEE Electron Device Letters, Volume 21, Number 2, pages 63-65, Feb 2000.	Already of Record
	1-10	3-2004	Fakhr et al., "GaAs MISFETs With Insulating Gate Films Formed by Direct Oxidation and by Oxidation for Recessed GaAs Surfaces	Already of Record
	0-1	4/28/1965	DECK et al., "Gallium Arsenide MOS Transistors", Solid-State Electronics, 1965, Vol. 9, pp. 613-622, Great Britain.	Already of Record
	0-2	12/3/1995	PASSLACK et al., "C-V and G-V Characterization of In-Situ Fabricated Ga ₂ O ₃ -GaAs Interfaces for Inversion/Accumulation Device and Surface Passivation Applications," Solid-State Electronics, 1996, Vol. 39, No. 8, pp. 1133-1136, Great Britain.	Already of Record
	0-3	2/19/1996	PASSLACK et al., "Quasistatic and high frequency capacitance-voltage characterization of Ga ₂ O ₃ -GaAs structures fabricated by in-situ molecular beam epitaxy," Applied Physics Letters, Volume 68, Number 8, pages 1099-1101, 19 February 1996.	Already of Record
	0-4	1996	PASSLACK et al., "GaAs Surface Passivation Using in-Situ Oxide Deposition," Applied Surface Science, 1996, pp. 441-447.	Already of Record
	0-5	6-1995	PASSLACK et al., "Infrared Microscopy Studies on High-Power AlGaAs-GaAs-InGaP Lasers with Ga ₂ O ₃ Pass Coatings," IEEE Journal of Selected Topics in Quantum Electronics, Vol. 1, No. 2, June 1995, pp. 116-118.	Already of Record
	0-6	12/15/1995	PASSLACK et al., "Capacitance-Voltage and Forward-Voltage Characterization of AlGaAs-GaAs Structures," J. Appl. Phys., Vol. 78, No. 12, December 15, 1995, pp. 7091-7096.	Already of Record
	0-7	1997	HONG et al., "Novel Ga ₂ O ₃ (Ga ₂ O ₃) Passivation Techniques to Produce Low-Dielectric GaAs Interfaces," Journal of Crystal Growth, 1997, pp. 422-427.	Already of Record
	0-8	5/1/1996	HONG et al., "Low Interface State Density Oxide-GaAs Structures Fabricated by in-Situ Molecular Beam Epitaxy," J. Vac. Sci. Technol. B, Vol. 14, No. 3, May/June 1996, pp. 2297-2300.	Already of Record

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DNL	0-9	2/1/1997	PASSELACK et al, "Low Bit, Thermodynamically Stable $\text{Ga}_{2}\text{O}_{3}$ -GaAs Interfaces: Fabrication, Characterization, and Modeling," IEEE Transactions on Electron Devices, Vol. 44, No. 2, February 1997, pp. 274-285.	Already of Record
	0-10	12/21/2004	European Patent Office Supplementary European Search Report for application number EP01956104.	
Date: 06-15-05		Examiner's Signature: <i>Karyn Mungler</i>		

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Printed: February 17, 2005 (11:44am)

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